

ABSTRACTED-PUB-NO: JP 08274344A

BASIC-ABSTRACT:

The method involves accelerated p-type impurity ions into the channel formation area of a semiconductor material at a temperature of about 50-500 deg C.

ADVANTAGE - Performs homogeneous doping process. Promotes crystallization of Si thereby preventing shift of threshold voltage of TFT.

ABSTRACTED-PUB-NO: US 6165876A

EQUIVALENT-ABSTRACTS:

The method involves accelerated p-type impurity ions into the channel formation area of a semiconductor material at a temperature of about 50-500 deg C.

ADVANTAGE - Performs homogeneous doping process. Promotes crystallization of Si thereby preventing shift of threshold voltage of TFT.

CHOSEN-DRAWING: Dwg.2/9

TITLE-TERMS: DOPE METHOD PRODUCE SEMICONDUCTOR DEVICE THIN  
FILM TRANSISTOR LCD  
DEVICE IMPLANT DOPE ION CHANNEL FORMATION AREA  
SEMICONDUCTOR  
MATERIAL TEMPERATURE DEGREE

DERWENT-CLASS: L03 U11

CPI-CODES: L03-G05B; L04-C02B; L04-E01;

EPI-CODES: U11-C02B2; U11-C02J6; U11-C18A1;

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TITLE: Doping method for production of  
semiconductor device e.g. thin film transistor used in LCD  
device - implants dopant ions to channel formation area  
of semiconductor material at temperature of about  
50-500 deg C

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US 6165876 A		December 26, 2000	N/A
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